



POWER SKY (H.K.) LTD.

TO-92 Plastic-Encapsulate Transistors

M8050 TRANSISTOR (NPN)

FEATURES

Power dissipation

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	800	mA
P_C	Collector Power Dissipation	625	mW
T_J	Junction Temperature	125	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-125	$^\circ\text{C}$

TO-92

1.EMITTER

2. BASE

3. COLLECTOR



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

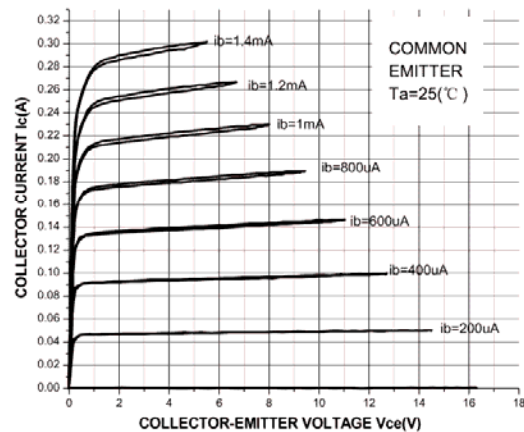
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	40		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=1\text{mA}, I_B=0$	25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	6		V
Collector cut-off current	I_{CBO}	$V_{CB}=35\text{V}, I_E=0$		0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=20\text{V}, I_B=0$		0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=1\text{V}, I_C=5\text{mA}$	45		
	$h_{FE(2)}$	$V_{CE}=1\text{V}, I_C=100\text{mA}$	80	400	
	$h_{FE(3)}$	$V_{CE}=1\text{V}, I_C=800\text{mA}$	40		
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=800\text{mA}, I_B=80\text{mA}$		0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=800\text{mA}, I_B=80\text{mA}$		1.2	V
Transition frequency	f_T	$V_{CE}=6\text{V}, I_C=20\text{mA}, f=30\text{MHz}$	150		MHz

* Pulse Test : pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

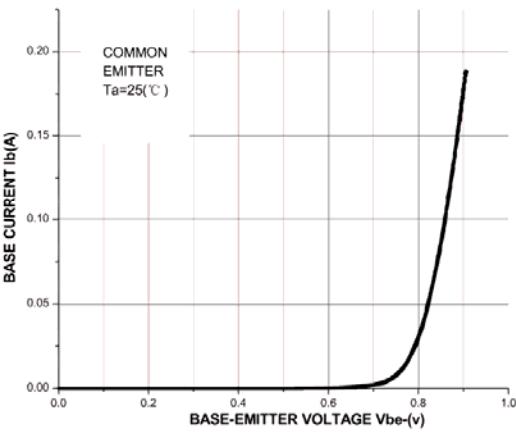
Typical Characteristics

M8050

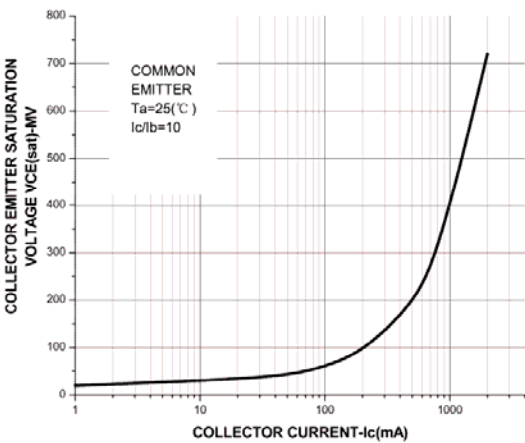
Ic-Vce



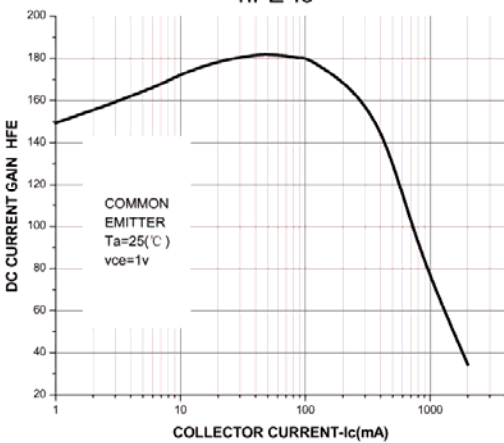
Ib-Vbe



Vcesat-Ic



hFE-Ic



Pc-Ta

